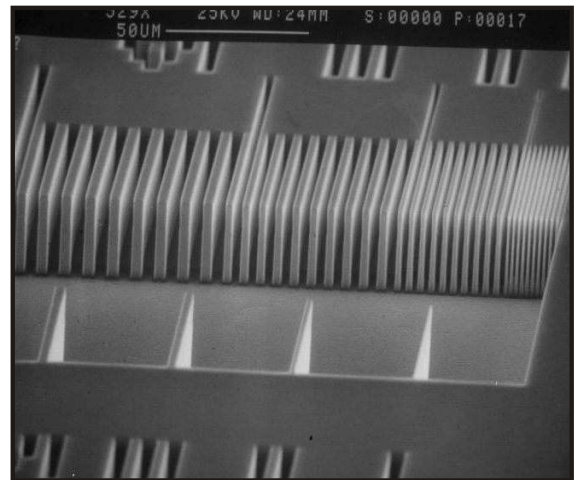
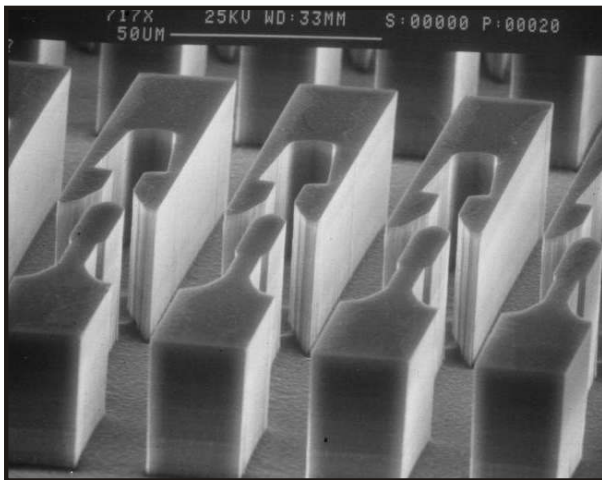
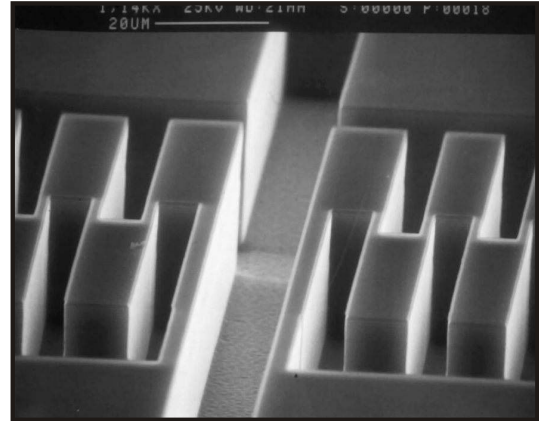
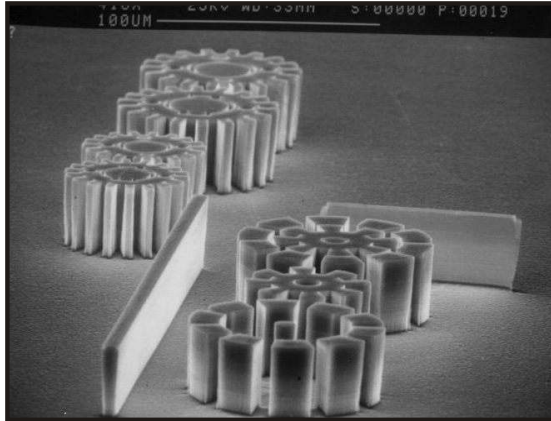


# Plasmalab Data

## Si etching: the “Bosch Process”



etched at the OPT application lab, Yatton (UK)

### Equipment: *Plasmalab System 100 (Cluster)*

#### Technology:

- Reactive Ion Etching
- Inductive Coupled Plasma Source
- room temperature process
- He backside cooling

#### Results:

- Rate : up to 10  $\mu\text{m}/\text{min}$
- Uniformity:  $\leq \pm 2/3\%$  (4/6")
- anisotropic etch
- aspect ratio up to 30 : 1
- controllable wall profile
- high selectivity to Resist (> 75:1) and  $\text{SiO}_2$  (>> 100:1)

